

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of:

Chou

Serial No.: 10/724,657

Filed: December 1, 2003

Confirmation No. 2331

Group Art Unit: 2829

Examiner: Nguyen, Jimmy

TKHR Ref. 250507-1010

Tsai, Lee & Chen ref. NP-1855-US

For: **MEMORY DEVICE AND METHOD FOR BURN-IN TEST**

AMENDMENT AND RESPONSE TO OFFICE ACTION

Mail Stop – Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Sir:

The Office Action mailed on September 21, 2005, has been carefully considered. In response thereto, Applicant hereby submits the following amendments and remarks.

Please substitute the following amended abstract for the originally filed abstract:

A memory device and a method for burn in test are described. ~~The memory device has~~
characterized by a plurality of sub-array word line leak-current limited units and a plurality of single word line leak-current limited units. They are used to limit the current in each word line to a predetermined word line current value. In burn-in test mode, the output of a word line driver is kept in a high impedance state. The bit line stress voltage is applied to the row of memory cells through a normal read-write path. A voltage generator for generating a substantially stable voltage is also provided. In burn-in test mode, the even word lines and the odd word lines are grouped separately and the word line stress voltage is applied to the even word lines and to the odd word lines alternately.